# 74LVC2G241

# Dual buffer/line driver; 3-state

Rev. 12 — 22 June 2012

**Product data sheet** 

### 1. General description

The 74LVC2G241 is a dual non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs  $1\overline{OE}$  and  $2\overline{OE}$ :

- A HIGH level at pin 1 OE causes output 1Y to assume a high-impedance OFF-state.
- A LOW level at pin 2OE causes output 2Y to assume a high-impedance OFF-state.

Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of the 74LVC2G241 as a translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

### 2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V
- $\pm$  24 mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



# 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G241DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G241DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G241GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1
74LVC2G241GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74LVC2G241GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3\times2\times0.5$ mm	SOT996-2
74LVC2G241GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 $\times$ 1.6 $\times$ 0.5 mm	SOT902-2
74LVC2G241GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 $\times$ 1.0 $\times$ 0.35 mm	SOT1116
74LVC2G241GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

## 4. Marking

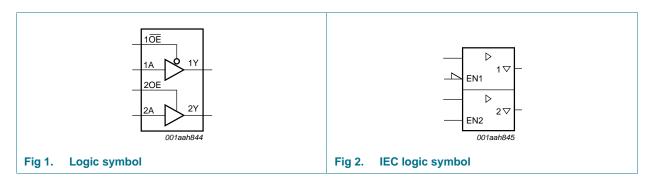
Table 2. Marking codes

Type number	Marking code <sup>[1]</sup>
74LVC2G241DP	V241
74LVC2G241DC	V41
74LVC2G241GT	V41
74LVC2G241GF	V1
74LVC2G241GD	V41
74LVC2G241GM	V41
74LVC2G241GN	V1
74LVC2G241GS	V1

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

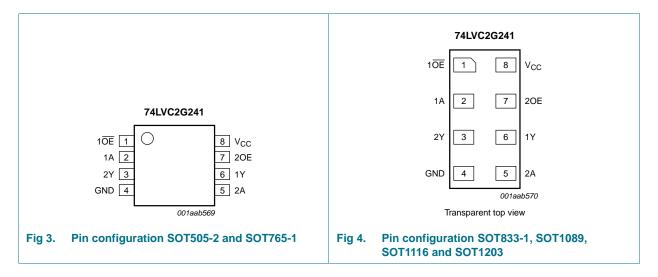
Product data sheet

## 5. Functional diagram

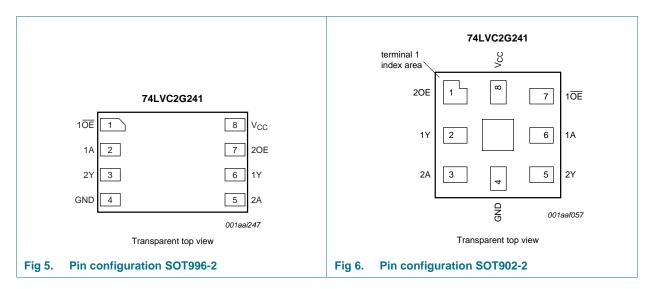


# 6. Pinning information

### 6.1 Pinning



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### 6.2 Pin description

Table 3. Pin description

**NXP Semiconductors** 

Symbol	Pin	Pin				
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2				
1 <del>OE</del>	1	7	output enable input (active LOW)			
1A, 2A	2, 5	6, 3	data input			
GND	4	4	ground (0 V)			
1Y, 2Y	6, 3	2, 5	data output			
20E	7	1	output enable input (active HIGH)			
$V_{CC}$	8	8	supply voltage			

# 7. Functional description

Table 4. Function table[1]

				Output	
1OE	1A	20E	2A	1Y	2Y
L	L	Н	L	L	L
L	Н	Н	Н	Н	Н
Н	X	L	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

74LVC2G241

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		[ <u>1</u> ] -0.5	+6.5	V
I <sub>OK</sub>	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
Vo	output voltage	enable mode	<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
		disable mode	<u>[1]</u> –0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
Io	output current	$V_O = 0 V to V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
I <sub>GND</sub>	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	<u>[3]</u> _	300	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	V <sub>CC</sub> = 1.65 V to 5.5 V; enable mode	0	$V_{CC}$	V
		V <sub>CC</sub> = 1.65 V to 5.5 V; disable mode	0	5.5	V
		V <sub>CC</sub> = 0 V; Power-down mode	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 1.65 V to 2.7 V	-	20	ns/V
		V <sub>CC</sub> = 2.7 V to 5.5 V	-	10	ns/V

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<sup>[2]</sup> When  $V_{CC} = 0 \text{ V}$  (Power-down mode), the output voltage can be 5.5 V in normal operation.

<sup>[3]</sup> For TSSOP8 packages: above 55 °C the value of P<sub>tot</sub> derates linearly at 2.5 mW/K.
For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly at 8.0 mW/K.
For XSON8, XSON8U and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

### 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
$T_{amb} = -$	40 °C to +85 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.3	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -100 \mu A$ ; $V_{CC} = 1.65 V$ to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	V
I	input leakage current	$V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μΑ
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	±0.1	±10	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND}; I_O = 0 \text{ A};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.1	10	μΑ
$\Delta I_{CC}$	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μΑ
C <sub>I</sub>	input capacitance		-	2	-	pF

**Table 7. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T <sub>amb</sub> = -	-40 °C to +125 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{\text{CC}}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -100 \ \mu A; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V
l <sub>l</sub>	input leakage current	$V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±20	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	-	±20	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	-	±20	μΑ
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND}; I_O = 0 \text{ A};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	40	μΑ
Δl <sub>CC</sub>	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to } 5.5 \text{ V}$	-	-	5	mΑ

<sup>[1]</sup> Typical values are measured at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C.

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# 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	rameter Conditions		0 °C to +85 °	,C	–40 °C to	-40 °C to +125 °C U	
			Min	Typ[1]	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7			'	'	'	'
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	4.5	8.8	1.0	11.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	2.8	4.9	0.5	6.3	ns
		V <sub>CC</sub> = 2.7 V	1.0	2.8	4.7	1.0	5.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	2.6	4.3	0.5	5.4	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	2.1	3.7	0.5	4.6	ns
t <sub>en</sub>	enable time	1OE to 1Y; see Figure 8						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.5	5.2	9.9	1.5	12.4	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	3.1	5.6	1.0	7.0	ns
		V <sub>CC</sub> = 2.7 V	1.5	3.2	5.5	1.5	6.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	2.7	4.7	0.5	5.9	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.5	2.0	3.8	0.5	4.8	ns
		2OE to 2Y; see Figure 9						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	4.3	8.8	1.0	11.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.0	2.7	4.7	1.0	5.9	ns
		V <sub>CC</sub> = 2.7 V	1.0	2.7	4.6	1.0	5.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.5	4.1	1.0	5.1	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	1.9	3.3	0.5	4.1	ns
t <sub>dis</sub>	disable time	1OE to 1Y; see Figure 8						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.0	3.2	11.6	1.0	14.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.5	2.2	5.8	0.5	7.6	ns
		V <sub>CC</sub> = 2.7 V	1.0	2.8	4.6	1.0	5.9	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	2.6	4.4	1.0	5.7	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	2.0	3.4	0.5	4.6	ns
		2OE to 2Y; see Figure 9						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	3.6	12.5	1.0	15.2	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.5	2.0	5.2	0.5	6.9	ns
		V <sub>CC</sub> = 2.7 V	1.5	3.2	4.9	1.5	6.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.8	4.2	1.0	5.4	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	2.0	3.3	0.5	4.4	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		-40 °C to +85 °C		–40 °C to	+125 °C	Unit	
				Min	Typ[1]	Max	Min	Max	
C <sub>PD</sub> power dissipation capacitance		per buffer; $V_I = GND$ to $V_{CC}$	[5]						
		output enabled		-	20	-	-	-	pF
		output disabled		-	5	-	-	-	pF

- [1] Typical values are measured at nominal  $V_{CC}$  and at  $T_{amb}$  = 25 °C.
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .
- [4]  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .
- [5]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

### 12. Waveforms

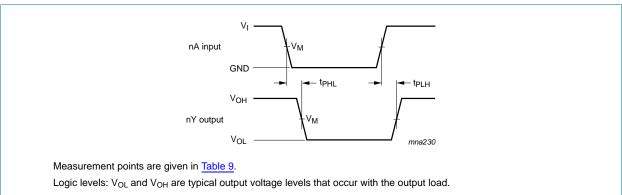


Fig 7. The data input (nA) to output (nY) propagation delays

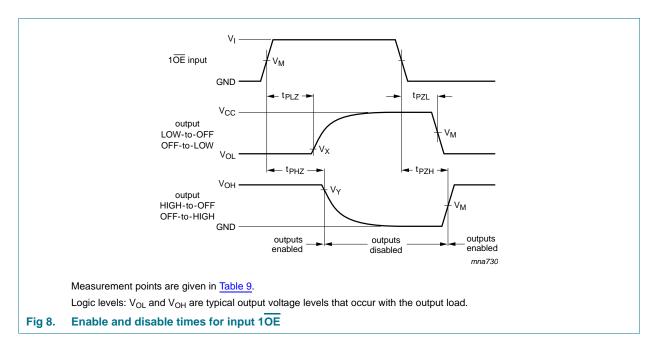
Table 9. Measurement points

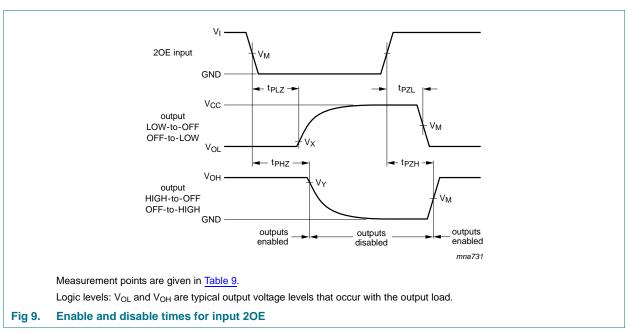
Supply voltage	Input	Output	Output				
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>			
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{\text{CC}}$	V <sub>OL</sub> + 0.15 V	$V_{OH}-0.15\ V$			
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{\text{CC}}$	$V_{OL} + 0.15 V$	$V_{OH} - 0.15 V$			
2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$			
3.0 V to 3.6 V	1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	$V_{OH} - 0.3 V$			
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.3 V	$V_{OH} - 0.3 V$			

74LVC2G241

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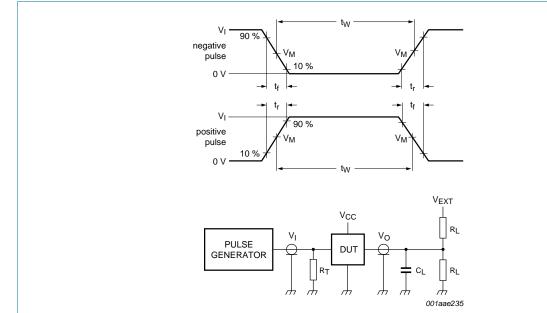
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Test data is given in Table 10.

Definitions for test circuit:

R<sub>L</sub> = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $V_{EXT}$  = Test voltage for switching times.

Fig 10. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input	Load	Load V <sub>EXT</sub>				Load		
	VI	CL	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	$t_{PZL}$ , $t_{PLZ}$			
1.65 V to 1.95 V	$V_{CC}$	30 pF	1 kΩ	open	GND	$2 \times V_{CC}$			
2.3 V to 2.7 V	$V_{CC}$	30 pF	500 Ω	open	GND	$2 \times V_{CC}$			
2.7 V	2.7 V	50 pF	$500~\Omega$	open	GND	6 V			
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V			
4.5 V to 5.5 V	$V_{CC}$	50 pF	500 Ω	open	GND	$2 \times V_{CC}$			

# 13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

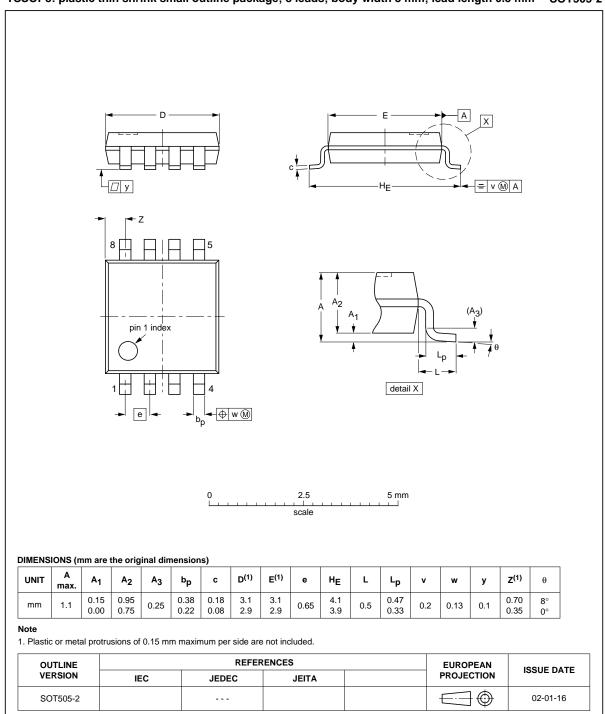


Fig 11. Package outline SOT505-2 (TSSOP8)

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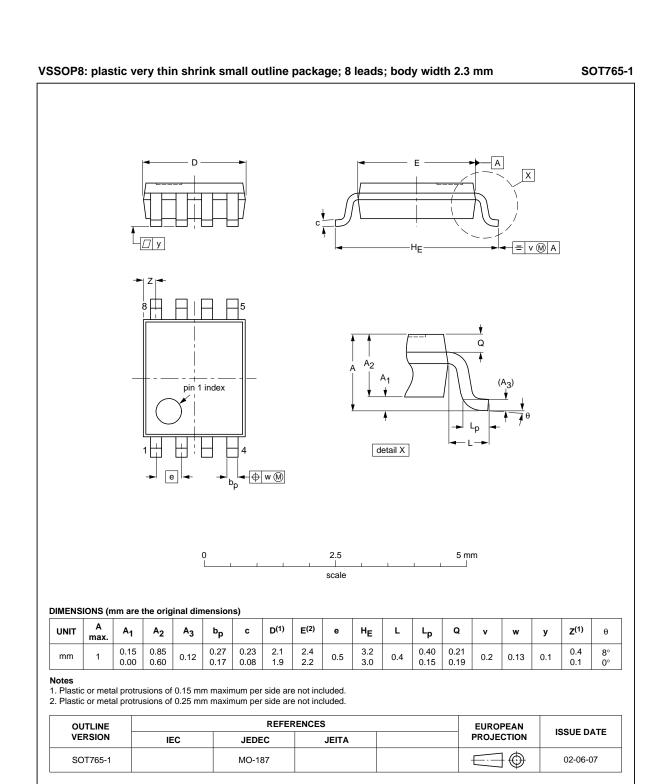


Fig 12. Package outline SOT765-1 (VSSOP8)

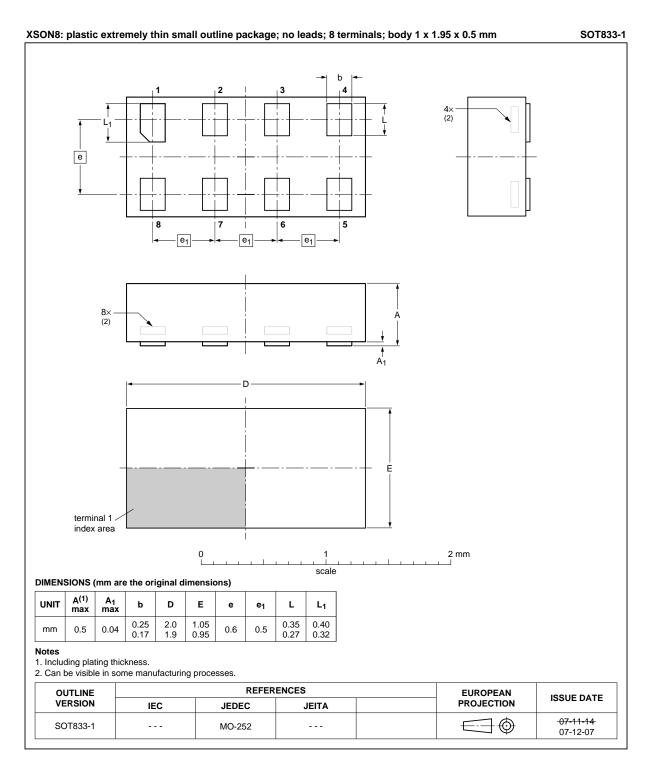


Fig 13. Package outline SOT833-1 (XSON8)

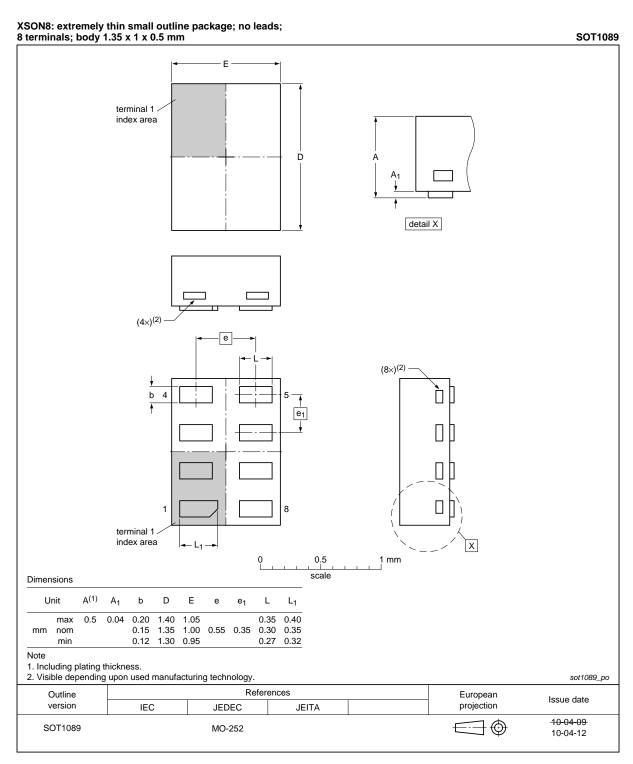


Fig 14. Package outline SOT1089 (XSON8)

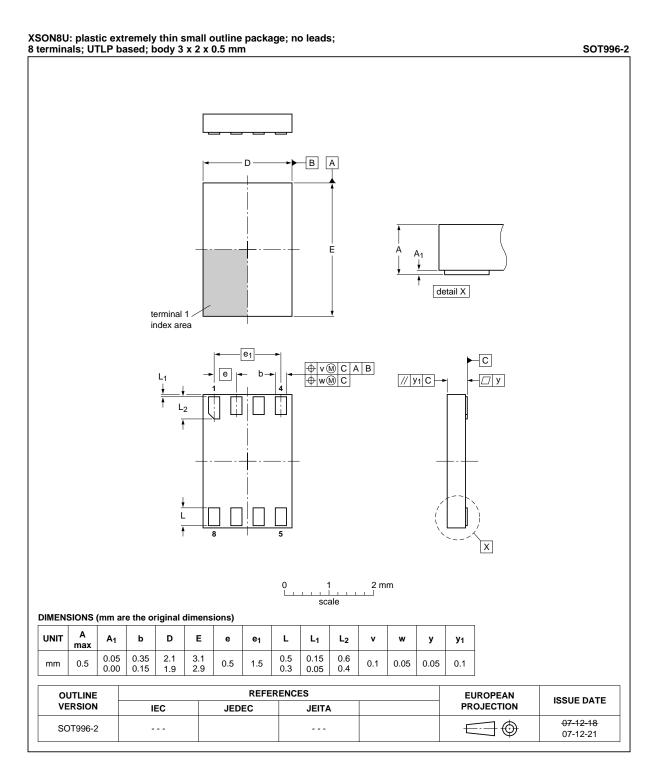


Fig 15. Package outline SOT996-2 (XSON8U)

**Product data sheet** 

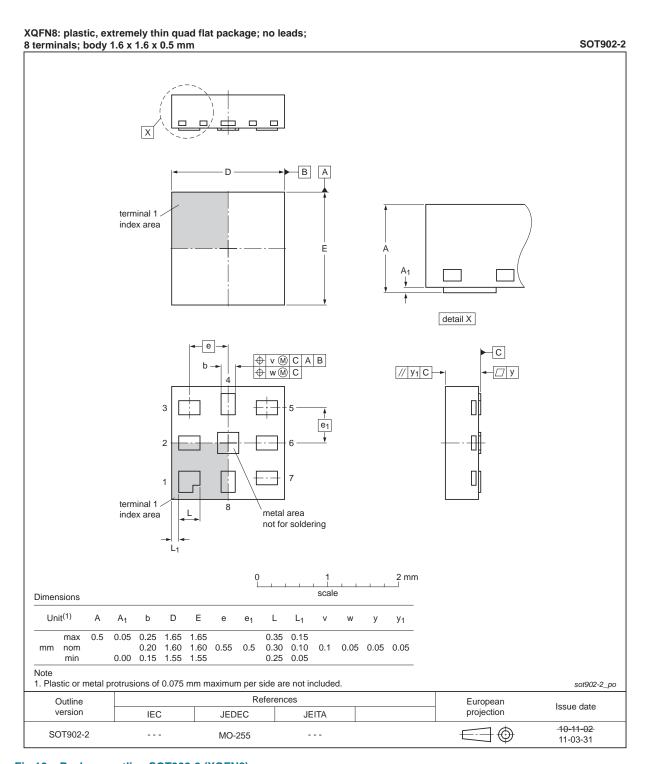


Fig 16. Package outline SOT902-2 (XQFN8)

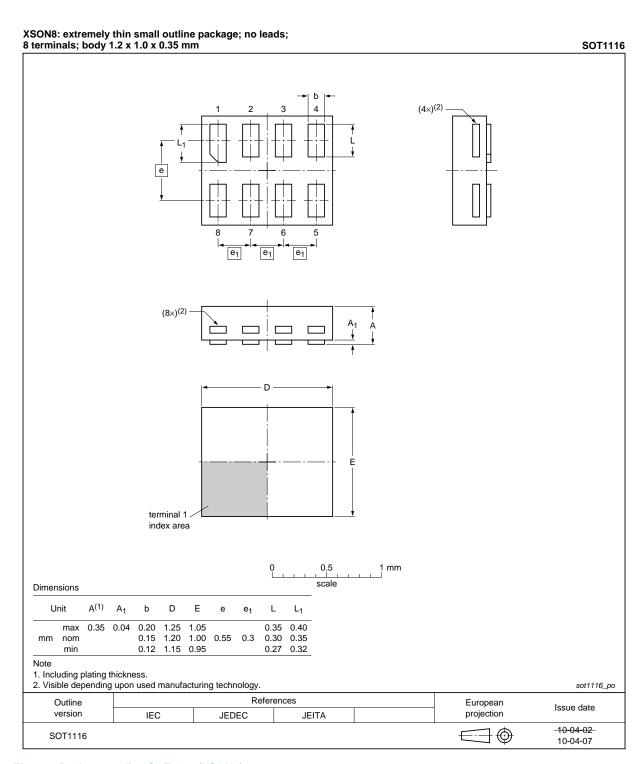


Fig 17. Package outline SOT1116 (XSON8)

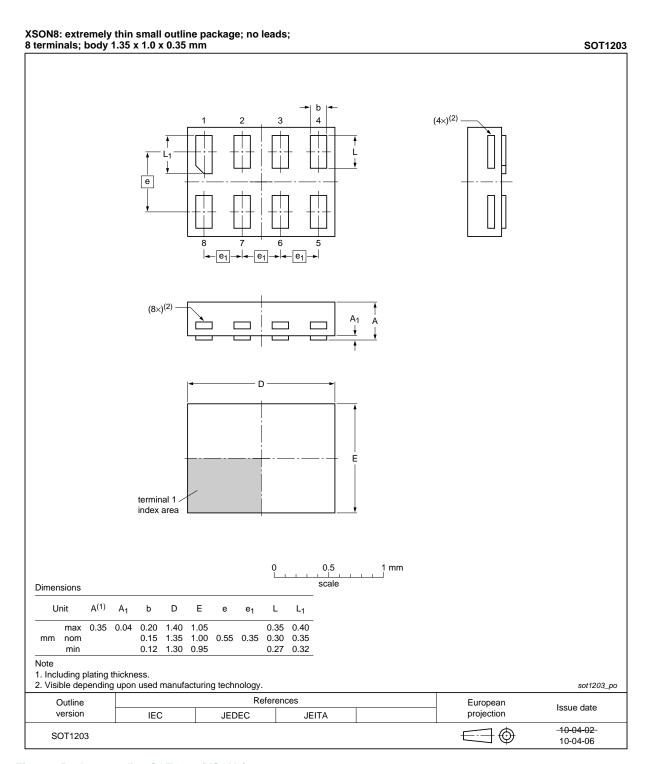


Fig 18. Package outline SOT1203 (XSON8)

### 14. Abbreviations

### Table 11. Abbreviations

Acronym	Description	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

## 15. Revision history

### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74LVC2G241 v.12	20120622	Product data sheet	-	74LVC2G241 v.11	
Modifications:	<ul> <li>For type number 74LVC2G241GM the SOT code has changed to SOT902-2.</li> </ul>				
74LVC2G241 v.11	20111129	Product data sheet	-	74LVC2G241 v.10	
Modifications:	Legal pages updated.				
74LVC2G241 v.10	20100806	Product data sheet	-	74LVC2G241 v.9	
74LVC2G241 v.9	20080610	Product data sheet	-	74LVC2G241 v.8	
74LVC2G241 v.8	20080312	Product data sheet	-	74LVC2G241 v.7	
74LVC2G241 v.7	20071005	Product data sheet	-	74LVC2G241 v.6	
74LVC2G241 v.6	20060922	Product data sheet	-	74LVC2G241 v.5	
74LVC2G241 v.5	20050202	Product specification	-	74LVC2G241 v.4	
74LVC2G241 v.4	20040922	Product specification	-	74LVC2G241 v.3	
74LVC2G241 v.3	20030311	Product specification	-	74LVC2G241 v.2	
74LVC2G241 v.2	20030129	Product specification	-	74LVC2G241 v.1	
74LVC2G241 v.1	20021030	Product specification	-	-	

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors 74LVC2G241

#### Dual buffer/line driver; 3-state

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Product data sheet

# 74LVC2G241

### Dual buffer/line driver; 3-state

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